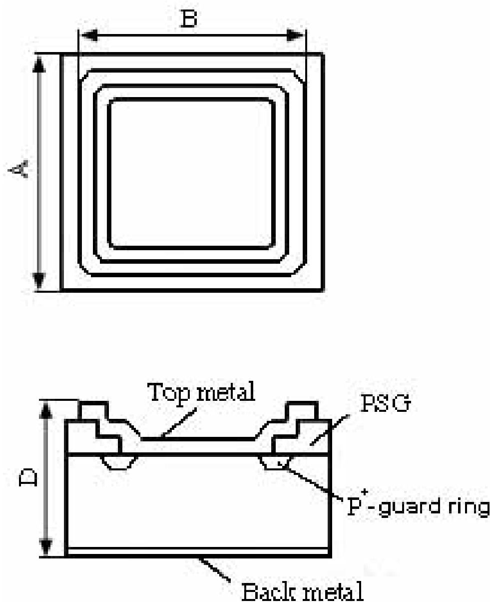
SCHOTTKY DIODES KDN-01040B.

Rev.1. Feb. 2010

VSP-MIKRON	**1A/40V.** Die Size-39mil.			
Electrical Characteristics	**Symbol**	**Unit**	**Spec. limit**	**Die Sort**
Breakdown Voltage @ I_R=10mA	V_{BR}	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	1,0	-
DC Forward Voltage @ 25˚C, I_F=1,0A @ 25˚C, I_F=2,0A	V_F	V	0,48 0,58	0,46 0,56
Maximum Reverse Current @ 25˚C, V_R=45V @ 25˚C, V_R=40V 125˚C, V_R=40V	I_R	mA	- 0,060 15,0	0,060 0,040 13,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	40	-
Peak Repetitive Reverse Surge Current @2,0μs, f=1kHz., T_J<150˚C.	I_{RRM}	A	1,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/μS	10.000	
Operating Junction Temperature	T_J	˚C	150	



DIM	ITEM	μm
A_X A_y	Wafer Form Die Size	1000 1000
B_X B_y	Top Metal Size	860 860
D	Thickness	300max.
Scribe line Width		80

Top metal: a) **Al-Ni-Ag** – for Soldering;

b) **Al** – for Wire Bond.

Backside metal: **Ti-Ni-Ag**.

www.vsp-mikron.com